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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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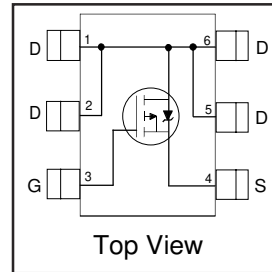
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Si3443DV

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- -2.5V Rated

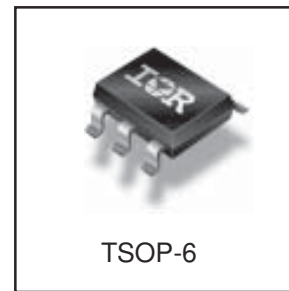


$V_{DSS} = -20V$
$R_{DS(on)} = 0.065\Omega$

Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The TSOP-6 package with its customized leadframe produces a HEXFET® power MOSFET with $R_{DS(on)}$ 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. It's unique thermal design and $R_{DS(on)}$ reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.4	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.5	
I_{DM}	Pulsed Drain Current ①	-20	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
E_{AS}	Single Pulse Avalanche Energy②	31	mJ
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

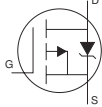
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	62.5	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.005	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.034	0.065	Ω	$V_{GS} = -4.5V, I_D = -4.4A$ ②
		—	0.053	0.090		$V_{GS} = -2.7V, I_D = -3.7A$ ②
		—	0.060	0.100		$V_{GS} = -2.5V, I_D = -3.5A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.60	—	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	—	12	—	S	$V_{DS} = -10V, I_D = -4.4A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
		—	—	-5.0		$V_{DS} = -20V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	11	15	nC	$I_D = -4.4A$
Q_{gs}	Gate-to-Source Charge	—	2.2	—		$V_{DS} = -10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.9	—		$V_{GS} = -4.5V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	12	50	ns	$V_{DD} = -10V, V_{GS} = -4.5V$ ②
t_r	Rise Time	—	33	60		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	70	100		$R_G = 6.0\Omega$
t_f	Fall Time	—	72	100		$R_D = 10\Omega, \text{ ②}$
C_{iss}	Input Capacitance	—	1079	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	220	—		$V_{DS} = -10V$
C_{rss}	Reverse Transfer Capacitance	—	152	—		$f = 1.0\text{MHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-20		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.7A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 25^\circ\text{C}, I_F = -1.7A$
Q_{rr}	Reverse Recovery Charge	—	30	44	nC	$di/dt = -100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on FR-4 board, $t \leq 5\text{sec}$.
- ④ Starting $T_J = 25^\circ\text{C}, L = 6.8\text{mH}$
 $R_G = 25\Omega, I_{AS} = -3.0A$.

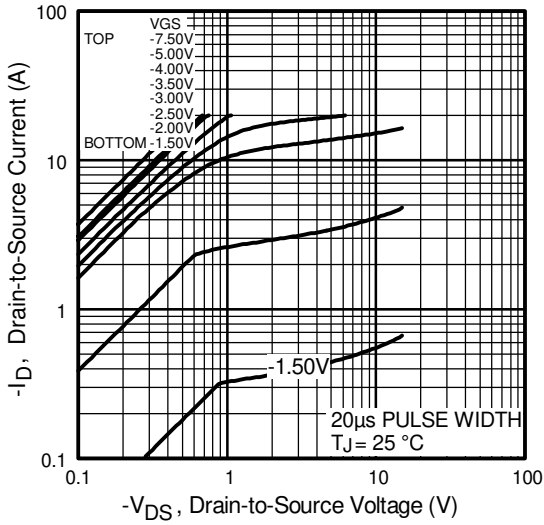


Fig 1. Typical Output Characteristics

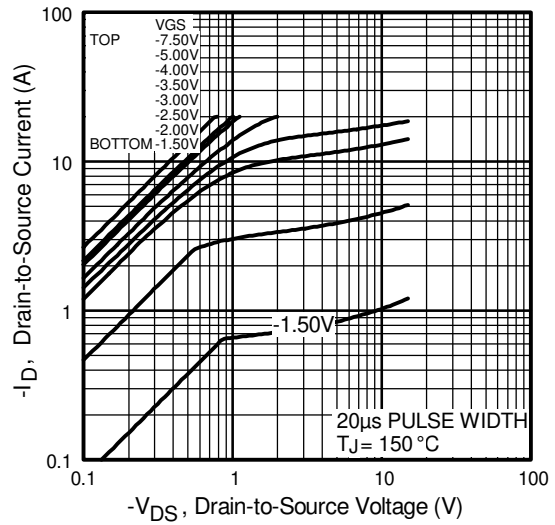


Fig 2. Typical Output Characteristics

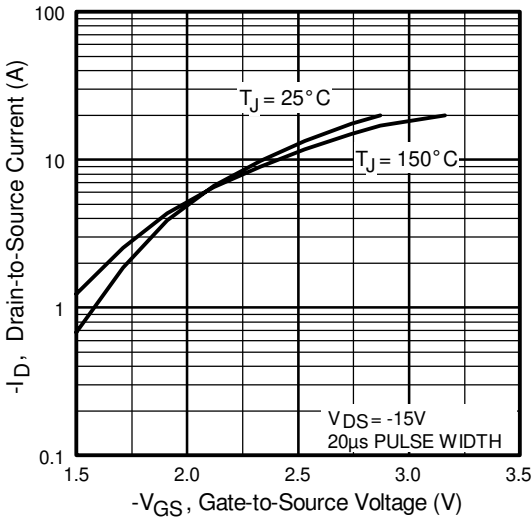


Fig 3. Typical Transfer Characteristics

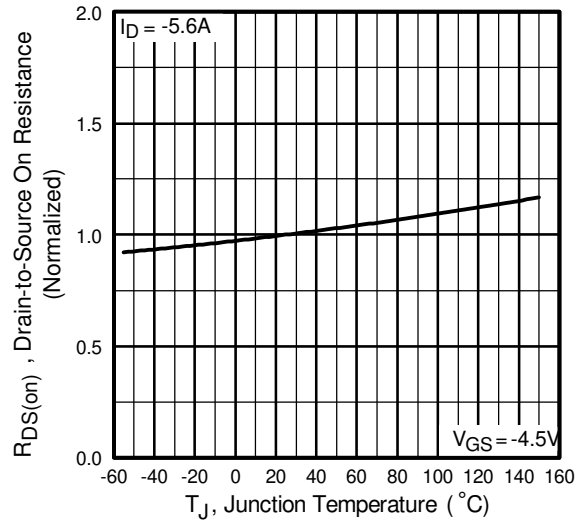


Fig 4. Normalized On-Resistance Vs. Temperature

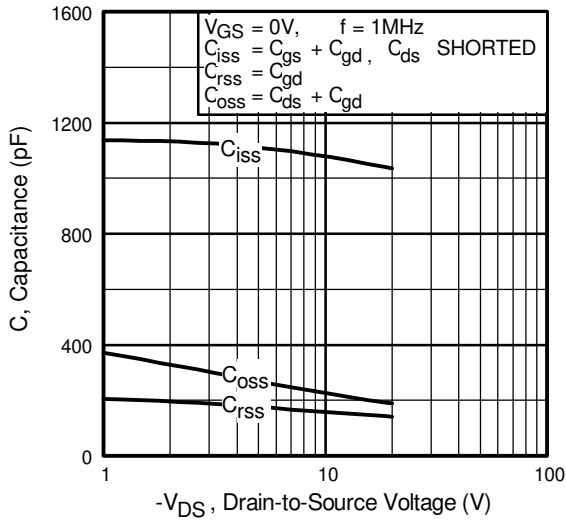


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

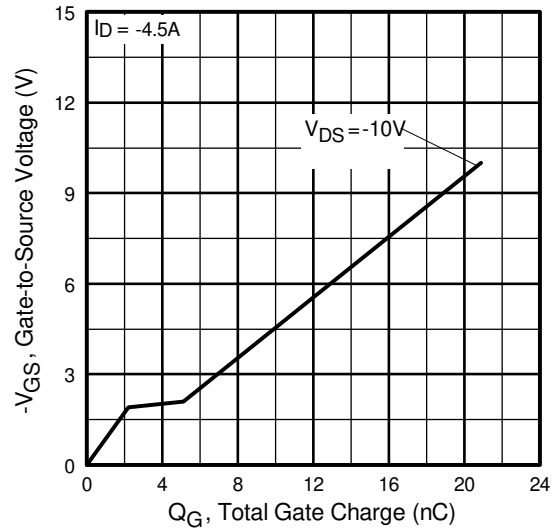


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

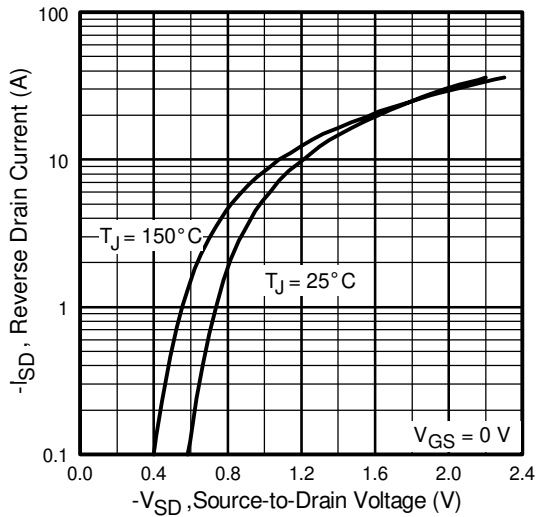


Fig 7. Typical Source-Drain Diode Forward Voltage

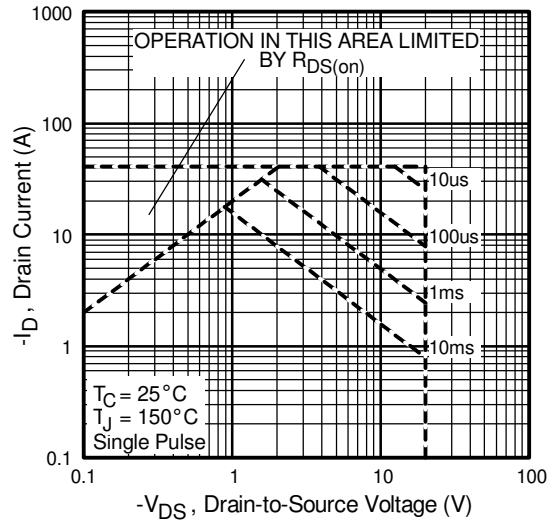


Fig 8. Maximum Safe Operating Area

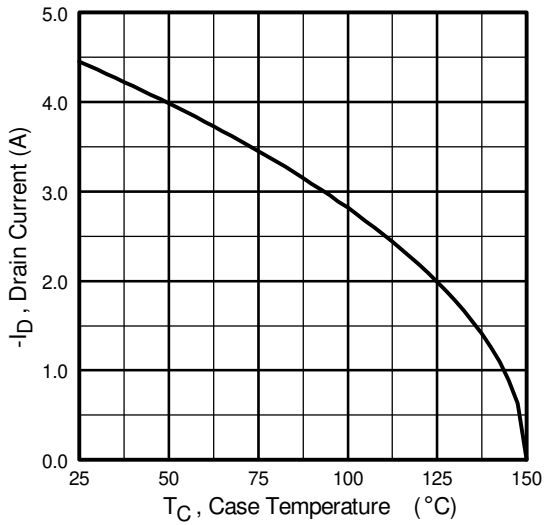


Fig 9. Maximum Drain Current Vs. Case Temperature

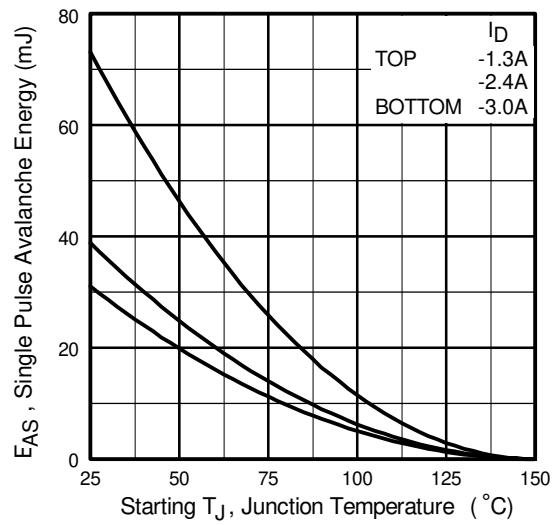


Fig 10. Maximum Avalanche Energy Vs. Drain Current

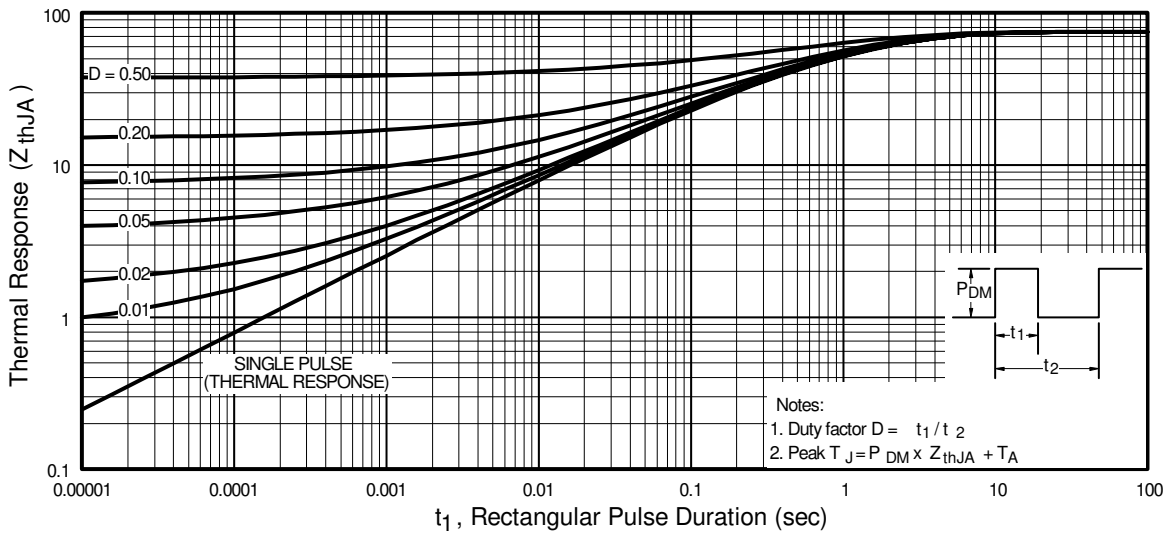


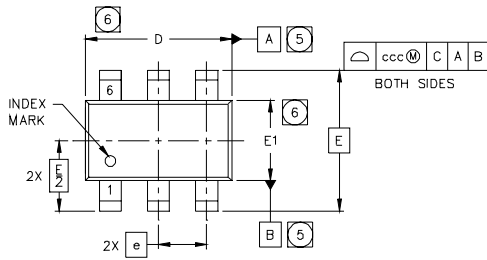
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Si3443DV

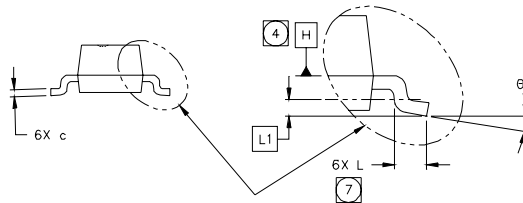
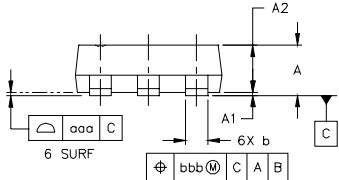
Package Outline

TSOP-6

International
IRF Rectifier



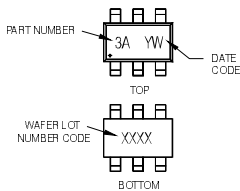
SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
θ	0°	---	8°	0°	---	8°
ccc	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		



Part Marking Information

TSOP-6

Notes: This part marking information applies to devices produced before 02/26/2001
EXAMPLE: THIS IS AN SI3443DV WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

PART NUMBER CODE REFERENCE:

- 3A = SI3443DV
- 3B = IRF5800
- 3C = IRF5850
- 3D = IRF5851
- 3E = IRF5852
- 3J = IRF5805
- 3J = IRF5806

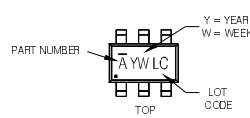
DATE CODE EXAMPLES:

- YWW = 9603 = 6C
- YWW = 9632 = FF

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Notes: This part marking information applies to devices produced after 02/26/2001
W = (1-26) F PRECEDED BY LAST DIGIT OF CALENDAR YEAR



YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

PART NUMBER CODE REFERENCE:

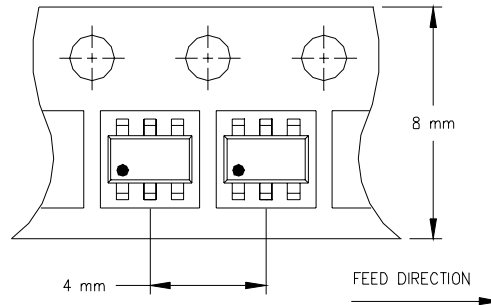
- A = SI3443DV
- B = IRF5800
- C = IRF5850
- D = IRF5851
- E = IRF5852
- J = IRF5805
- J = IRF5806
- K = IRF5810
- L = IRF5804
- N = IRF5803
- N = IRF5820

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

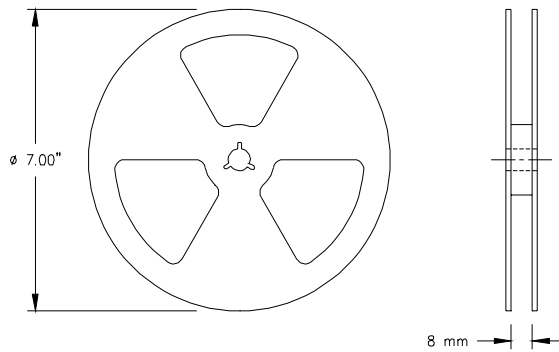
Tape & Reel Information

TSOP-6



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



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